# HIGH CMR, HIGH SPEED OPTO ISOLATOR



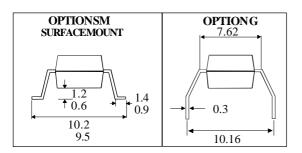
Dimensions in mm

#### DESCRIPTION

The ICPL 2611 consists of a GaAsP emitting diode and a unique integrated detector. The photons are detected by a photodiode and then amplified by a high gain linear amplifier that drives a logic gate with a strobable output. This output features a Schottky clamped open collector output transistor. The circuit is temperature, current and voltage compensated. This unique isolator design provides maximum DC and AC circuit isolation between input and output while achieving LSTTL/TTL circuit compatibility. The isolator operational parameters are guaranteed from 0°C to 70°C, such that a minimum input current of 5 mA will sink an eight gate fan-out (13mA) at the output with 5 volt Vcc supplied to the detector. This isolation and coupling is achieved with a typical propagation delay of 39ns. The enable input provides gating of the detector with input sinking and sourcing requirements compatible with LSTTL/TTL interfacing and a propagation delay of 35ns typical.

#### FEATURES

- LSTTL/TTL Compatible
- High Speed
- Low Input Current Required
- Guaranteed Performance over Temperature
- 2500 V<sub>RMS</sub> Withstand Test Voltage (1 Minute)
- Internal Shield for High Common Mode Rejection



#### v<sub>cc</sub> 8 1 E 7 2 [ 6.9 6.3 3 [ 6 4 □ $5_{GND}$ 1.3 \* ICPL2601 NOISE SHIELD 97 7.62 9.1 4.0 3.6 05 $15^{\circ}$ Max 0.3 $0.5^{-}$ 3

### TRUTHTABLE

- 2.54

INPUT	ENABLE	OUTPUT	A 0.1µF bypass
Н	Н	L	capacitor must be
L	Н	H	connected between
Н	L	Н	pins 8 and 5 (See
L	L	Н	note 1)

#### ABSOLUTE MAXIMUM RATINGS

#### (25 °C unless otherwise noted)

Storage Temperature	-55 to +125°C
Operating Temperature	$-0^{\circ}$ C to $+70^{\circ}$ C
Lead Solder Temperature	260°C for 10secs
(1.6mm below the seating plate)	

#### **INPUT DIODE**

Forward Current	20mA (2)	
Reverse Voltage _	5V	
Enable Voltage	5.5V	
(Not to exceed Vcc by	more that 500mV)	

#### **OUTPUT PHOTOTRANSISTOR**

Supply VoltageVcc	7V (1 Min Max)
Current - lo	25mA
Collector Power Dissipation	40mW
Collector Voltage - Vo	7V

All electrical parameters are 100 % tested Specifications are guaranteed to a cumulative 0.65% AQL

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PARAMETER	MIN	TYP*	MAX	UNITS	TEST CONDITIONS	FIG	NOTE
High Level Output Current I <sub>OH</sub>		7	250	μA	$Vcc = 5.5V$ , $Vo = 5.5V$ . IF = $250\mu A VE = 2.0V$		
Low Level Output Voltage V <sub>OL</sub>		0.4	0.6	V	Vcc =5.5V, IF = 5mA, VE = 2.0V $I_{0L}$ (sinking) = 13mA		
High Level Enable Current $I_{_{EH}}$		-1.0		mA	Vcc =5.5V, VE = 2.0V		
Low Level Enable Current $I_{EL}$		-1.6	-2.0	mA	Vcc = 5.5V, VE = 0.5V		
High Level Supply Current $I_{CCH}$		10	15	mA	Vcc = 5.5V, IF = 0, VE = 0.5V		
Low Level Supply Current $I_{CCL}$		15	19	mA	Vcc = 5.5V, IF = 10 mA, VE = 0.5V		
Input - Output Insulation Leakage Current - I <sub>10</sub>			1.0	μA	Relative Humidity = 45% TA = 25 °C, t = 5s, $V_{I0}$ = 3000 V DC mA,		3
Withstand Insulation Test Voltage V <sub>ISO</sub>	2500			V	$R_{\rm H} < 50\%, T_{\rm A} = 25^{\circ}C, t = 1 \text{ Min}$		3
Resistance - R <sub>IO</sub>		1012		ohm	$V_{I0} = 500V, t = 5s, T_A = 25 \ ^{\circ}C$		3
Capacitance - C <sub>IO</sub>		0.6		pF	$f = 1MHz$ , $TA = 25 \ ^{\circ}C$		3
Input Forward Voltage - V <sub>F</sub>		1.5	1.75	V	IF = 10mA, TA = $25^{\circ}$ C		
Input Reverse Breakdown Voltage - B <sub>VR</sub>	5			V	$Ir = 10 \ \mu A, TA = 25^{\circ}C$		
Input Capacitance - C <sub>IN</sub>		60		pF	$V_F = 0, f, = 1 MHz$		
Current Transfer Ratio - CTR		700		%	IF= 5mA, RL= $100\Omega$		12
High Level Enable Voltage - $V_{_{EH}}$	2.0			V	Vcc =5.5V, IF =10 mA		11
Low Level Enable Voltage - $V_{EL}$			0.8	V <sub>RMS</sub>	Vcc =5.5V, IF =10 mA		11
Input Diode TemperatureCoefficient $\Delta VF$		-1.4			IF = 10mA,		

#### ELECTRICAL CHARACTERISTICS (Over recommended temperature 0°C to70°C unless specified)

- \*All typicals are at  $V_{CC} = 5V$ ,  $T_A = 25^{\circ}C$ 1 Bypassing of the power supply line is required, with a 0.01  $\mu$  F ceramic disc capacitor adjacent to each isolator. The power supply bus for the isolator(s) should be seperate from the bus for any active loads. Otherwise a larger value of bypass capacitor (up to  $0.1 \ \mu$  F)may be needed to supress regenerative feedback via the power supply.
  - 2 Peaking circuits may produce transient input currents up to 50mA, 50ns maximum pulse width, provided average current does not exceed 20mA
  - 3 Device considered a two terminal device; pins 1, 2, 3, and 4 shorted together, and pins 5, 6, 7 and 8 shorted together.
  - The t  $_{PLH}$  propagation delay is measured from the 3.75 mA point on the trailing edge of the 4 input pulse to the 1.5V point on the trailing edge of the output pulse.
  - 5 The t pur propagation delay is measured from the 3.75mA point on the leading edge of the input pulse to 1.5V point on the leading edge of the output pulse.
  - The t<sub>ELH</sub>enable propagation delay is measured from the 1.5V point of the trailing edge of the 6 input pulse to the 1.5V point on the trailing edge of the output pulse.
  - 7 The t<sub>EHI</sub> enable propagation delay is measured from the 1.5V point on the leading edge of the input pulse to the 1.5V point on the leading edge of the output pulse.
  - 8  $CM_{\mu}$  is the maximum tolerable rate of rise of the common mode voltage to assure that the output will remain in a high logic state (ie Vout> 2.0V).
  - 9 CM, is the maximum tolerable rate of fall of the common mode voltage to assure that the output will remain in a low logic state (ie Vout< 0.8V)

For sinusoidal voltages 
$$\left(\frac{dv_{CM}}{dt}\right)_{max} = \pi f_{CM} V_{CM}(p-p)$$

- 11 No external pull up is required for a high logic state on the enable input.
- 12 DC current transfer ratio is defined as the ratio of the output collector current to the forward bias input current times 100%.

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PARAMETER	MIN	TYP*	MAX	UNITS	TEST CONDITIONS	FIG	NOTE
Propagation Delay to High Output		35	75	ns	$R_{t} = 350\Omega C_{t} = 15 pF,$		4
Level - t <sub>PLH</sub>					$1_{\rm F} = 7.5 {\rm mA}$		
Propagation Delay Time to Low		39	75	ns	$R_{L} = 350\Omega C_{L} = 15 \text{ pF},$		5
Output Level - t <sub>PHL</sub>					$I_F = 7.5 \text{mA}$		5
Output rise time (10 -90%) - t <sub>r</sub>		27		ns	$R_1 = 350\Omega C_1 = 15 pF$		
Output Fall Time (90 - 10% - $t_f$		16		ns	$I_{\rm F} = 7.5 \mathrm{mA}$		
Propagation Delay Time of		25		ns	$R_L = 350\Omega C_L = 15 pF,$		6
Enable from $V_{EH}$ to $V_{EL}$ - $t_{ELH}$					$I_{\rm F}$ = 7.5mA, $V_{\rm EH}$ = 3.0V, $V_{\rm EL}$ = 0		0
Propagation Delay time of Enable		14		ns	$R_L = 350 \ \Omega \ C_L = 15 \ pF,$		
from $V_{_{\rm EL}}$ to to $V_{_{\rm EH}}$ - t $_{_{\rm EHL}}$					$I_{\rm F} = 7.5 {\rm mA},  V_{\rm EH} = 3.0 {\rm V},  V_{\rm EL} = 0$		7
Common Mode Transient Immunity					$V_{CM} = 400 V \text{ (peak)}, R_{L} = 350 \Omega$		8,10
at High Output Level -CM <sub>H</sub>		12000		V/µs	$I_F = 0mA$ , Vo (min) = 2V		0,10
Common Mode Transient Immunity		11000		V/µs	$V_{CM} = 400 V \text{ (peak) } R_{L} = 350 \Omega$		9,10
at Low Output Level - $CM_L$					$I_F = 7.5 \text{mA}$ , Vo (max) = 0.8V		

# SWITCHING CHARACTERISTICS (AT $\rm T_{A}$ = 25°C, $\rm V_{cc}$ = 5V )

## **RECOMMENDED OPERATING CONDITIONS**

	SYM	MIN	MAX	UNITS
Current, Low Level	$\mathbf{I}_{\mathrm{FL}}$	0	250	μΑ
Input Current, High Level	$I_{_{ m FH}}$	6.3*	15	mA
High Level Enable Voltage	$V_{_{\rm EH}}$	2.0	V <sub>cc</sub>	V
Low Level Enable Voltage (Output High)	V <sub>EL</sub>	0	0.8	V
Supply Voltage, Output	V <sub>cc</sub>	4.5	5.5	V
Fan Out (TTL)	N		8	
Operating Temperature	T <sub>A</sub>	0	70	°C

\*6.3mA condition permits at least 20% CTR degradation guardband Initial switching threshold is 5mA or less

# TEST CIRCUIT FOR $\mathbf{t}_{\text{PHL}}$ AND $\mathbf{t}_{\text{PLH}}$

